VS-10TTS08PbF, VS-10TTS08-M3

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum average on-state current	I _{T(AV)}	T 110 °C 100° condu	6.5				
Maximum RMS on-state current	I _{T(RMS)}	1 _C = 112 G, 180 Conduc	$T_C = 112 ^{\circ}C$, 180° conduction half sine wave				
Maximum peak, one-cycle,		10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C		95	Α		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volta	age reapplied, T _J = 125 °C	110	i		
Maximum 12t for fusing	l ² t	10 ms sine pulse, rated V	_{RRM} applied, T _J = 125 °C	45	A2a		
Maximum I ² t for fusing	1-1	10 ms sine pulse, no volta	64	A ² s			
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no vo	640	A²√s			
Maximum on-state voltage drop	V _{TM}	6.5 A, T _J = 25 °C		1.15	V		
On-state slope resistance	r _t	- T _J = 125 °C		17.3	mΩ		
Threshold voltage	V _{T(TO)}			0.85	V		
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	V Detect V A/	0.05			
current	I _{RM} /I _{DM}	T _J = 125 °C	$T_J = 125 ^{\circ}\text{C}$ $V_R = \text{Rated } V_{RRM}/V_{DRM}$				
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		30	mA		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		50			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$		150	V/µs		
Maximum rate of rise of turned-on current	dl/dt		100	A/μs			

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	VV	
Maximum peak positive gate current	+I _{GM}		1.5	Α	
Maximum peak negative gate voltage	-V _{GM}		10	V	
Maximum required DC gate current to trigger	l _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	20	mA	
		Anode supply = 6 V, resistive load, T _J = 25 °C	15		
		Anode supply = 6 V, resistive load, T _J = 125 °C	10		
Marrian was reliand DC and	V _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	1.2		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	1	,,	
		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	V_{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.2		
Maximum DC gate current not to trigger	I_{GD}	ij = 125 C, v _{DRM} = nated value	0.1	mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8			
Typical reverse recovery time	t _{rr}	T _J = 125 °C	3	μs		
Typical turn-off time	t _q	1J = 125 C	100			



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5		
Maximum thermal resistance, junction to ambient		R _{thJA}		62 °C/W		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf · in)	
Marking device			Case style TO-220AB	10TTS08		

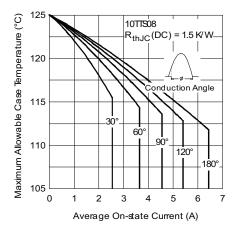


Fig. 1 - Current Rating Characteristics

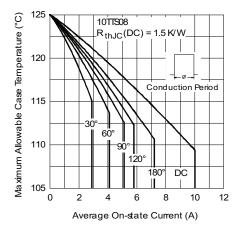


Fig. 2 - Current Rating Characteristic

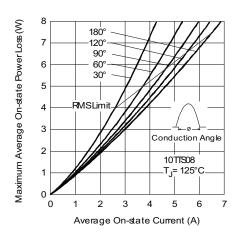


Fig. 3 - On-State Power Loss Characteristics

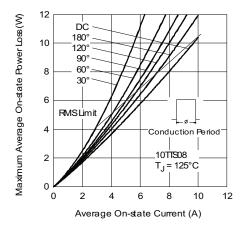


Fig. 4 - On-State Power Loss Characteristics

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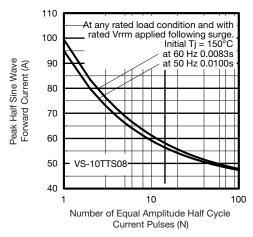


Fig. 5 - Maximum Non-Repetitive Surge Current

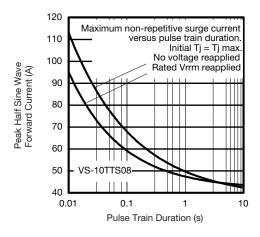


Fig. 6 - Maximum Non-Repetitive Surge Current

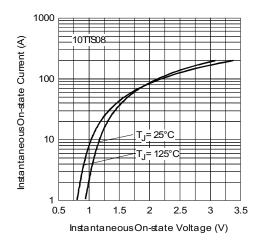


Fig. 7 - On-State Voltage Drop Characteristics

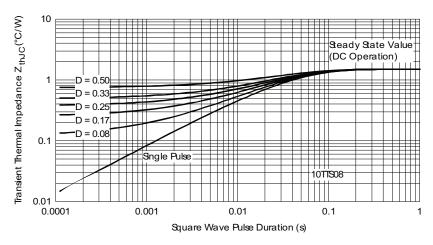


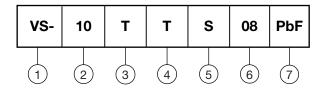
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-10TTS08PbF, VS-10TTS08-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM}

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-10TTS08PbF	50	1000	Antistatic plastic tubes		
VS-10TTS08-M3	50	1000	Antistatic plastic tubes		

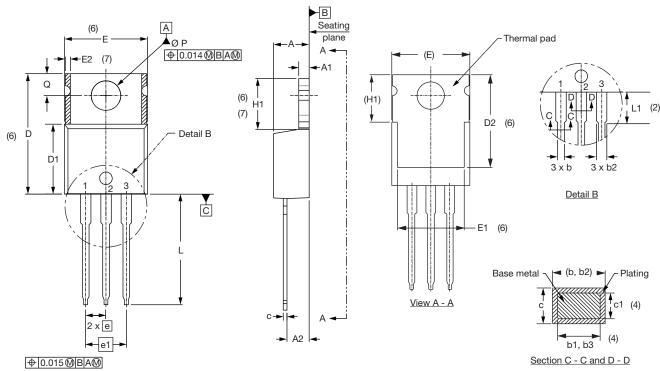
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225			
	TO-220AB -M3	www.vishay.com/doc?95028			



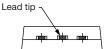
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TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments



- 1. Anode/open
- 2. Cathode
- 3. Anode

Diodes

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INC	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INC	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2		0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Legal Disclaimer Notice



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